

MA3S132D

Silicon epitaxial planar type

For switching circuits

■ Features

- Short reverse recovery time t_{rr}
- Small terminal capacitance, C_t
- Super-small SS-mini type package contained two elements, allowing high-density mounting

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter		Symbol	Rating	Unit
Reverse voltage (DC)		V_R	80	V
Peak reverse voltage		V_{RM}	80	V
Forward current (DC)	Single	I_F	100	mA
	Double		150	
Peak forward current	Single	I_{FM}	225	mA
	Double		340	
Non-repetitive peak forward surge current*	Single	I_{FSM}	500	mA
	Double		750	
Junction temperature		T_j	150	$^\circ\text{C}$
Storage temperature		T_{stg}	-55 to +150	$^\circ\text{C}$

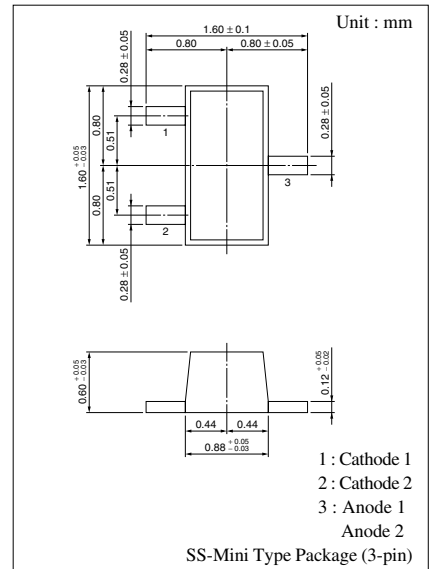
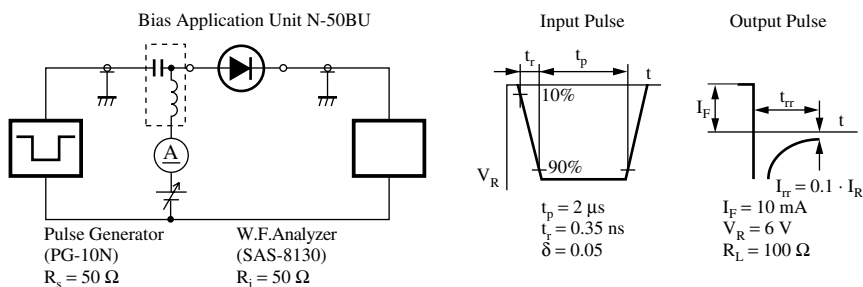
Note) * : $t = 1 \text{ s}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 75 \text{ V}$			100	nA
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100 \mu\text{A}$	80			V
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			15	pF
Reverse recovery time*	t_{rr}	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}$ $I_{tr} = 0.1 \cdot I_R, R_L = 100 \Omega$			10	ns

Note) 1. Rated input/output frequency: 100 MHz

2. * : t_{rr} measuring circuit



Marking Symbol: MO

Internal Connection

